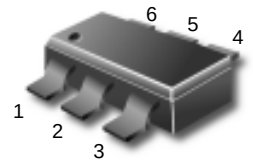
Silicon NPN Epitaxial Planer Transistor

L4501DW1T1



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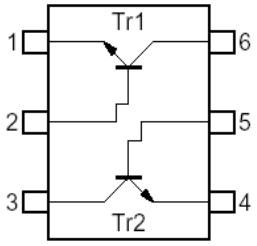
Feature

Pb-Free Package is available.

MAXIMUM RATINGS

Parameter	Symbol	Ratings	Unit
Collector-Emitter Voltage	V_{CEO}	50	V
Collector-Base Voltage	V_{CBO}	60	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector current-continuoun	IC	150	mAdc



THERMAL CHARATEERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) T_A=25°C	P_D	380	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	°C/W
Junction and Storage Temperature	Tj ,Tstg	-55 to +150	°C

DEVICE MARKING

L4501DW1T1=5H

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (IC=1mA)	V(BR)CEO	50	-	-	V
Emitter-Base Breakdown Voltage (IE=50μA)	V(BR)EBO	7	-	-	V
Collector-Base Breakdown Voltage (IC=50μA)	V(BR)CBO	60	-	-	V
Collector Cutoff Current (VCB=60V)	ICBO	-	-	0.1	μA

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EMITTER CUTOFF CURRENT VEB=7V	IEBO	-	-	0.1	μA

ON CHARACTERISTICS

DC Current Gain (IC=1mA, VCE=6.0V)	Hfe	120	-	560	
Collector-Emitter Saturation Voltage (IC=50mA,IB=5mA)	VCE(SAT)	-	-	0.4	V

SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product (VCE = 12.0V; IE =-2.0 mA,f=100MHZ)	Ft	-	180	-	MHz
Output Capacitance(VCE=12V,f=1.0MHz)	Cobo	-	2	3.5	Pf

ORDERING INFORMATION

Device	Marking	Shipping
L4501DW1T1	5H	3000/Tape&Reel
L4501DW1T1G	5H (Pb-Free)	3000/Tape&Reel

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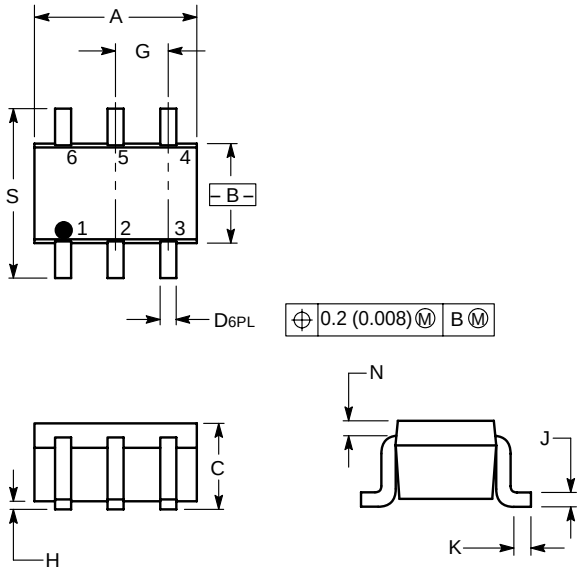

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1